# Power MOSFET for 1-2 Cells Lithium-ion Battery Protection

# 22 V, 3.55 m $\Omega$ , 25 A, Dual N-Channel

This Power MOSFET features a low on-state resistance. This device is suitable for applications such as power switches of portable machines. Best suited for 1-2 cells lithium-ion battery applications.

### **Features**

- 2.5 V Drive
- Common-Drain Type
- ESD Diode-Protected Gate
- This device is Pb-Free, Halogen Free and RoHS Compliance

# **Applications**

• 1-2 Cells Lithium-ion Battery Charging and Discharging Switch

# **Specifications**

# ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub> = 25°C)

Parameter	Symbol	Value	Unit
Source to Source Voltage	V <sub>SSS</sub>	22	V
Gate to Source Voltage	V <sub>GSS</sub>	±12	V
Source Current (DC)	I <sub>S</sub>	25	Α
Source Current (Pulse) PW ≤ 10 μs, duty cycle ≤ 1%	I <sub>SP</sub>	100	Α
Total Dissipation (Note 1)	P <sub>T</sub>	2.5	W
Junction Temperature	Tj	150	°C
Storage Temperature	T <sub>stg</sub>	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

# THERMAL RESISTANCE RATINGS

Parameter	Symbol	Value	Unit
Junction to Ambient (Note 1)	$R_{\theta JA}$	50	°C/W

<sup>1.</sup> Surface mounted on ceramic substrate (5000  $\text{mm}^2 \times 0.8 \text{ mm}$ ).

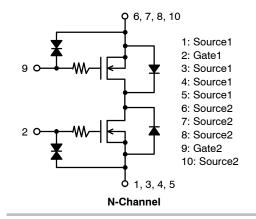


# ON Semiconductor®

# www.onsemi.com

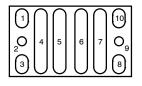
V <sub>SSS</sub>	R <sub>SS(ON)</sub> MAX	I <sub>S</sub> MAX
22 V	3.55 mΩ @ 4.5 V	25 A
	3.65 m $\Omega$ @ 3.8 V	
	5.3 mΩ @ 3.1 V	
	7.2 mΩ @ 2.5 V	

#### **ELECTRICAL CONNECTION**



## **PIN ASSIGNMENT**





# **MARKING DIAGRAM**

NZ AYWZZ

NZ = Specific Device Code A = Assembly Location

Y = Year
W = Work Week
ZZ = Assembly Lot

# **ORDERING INFORMATION**

See detailed ordering and shipping information on page 2 of this data sheet.

# **ELECTRICAL CHARACTERISTICS** $(T_A = 25^{\circ}C)$

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>(BR)SSS</sub>	Source to Source Breakdown Voltage	I <sub>S</sub> = 1 mA, V <sub>GS</sub> = 0 V	22			V
I <sub>SSS</sub>	Zero-Gate Voltage Source Current	V <sub>SS</sub> = 17.6 V, V <sub>GS</sub> = 0 V			1	μΑ
I <sub>GSS</sub>	Gate to Source Leakage Current	$V_{GS} = \pm 8 \text{ V}, V_{SS} = 0 \text{ V}$			±1	μΑ
V <sub>GS</sub> (th)	Gate Threshold Voltage	V <sub>SS</sub> = 10 V, I <sub>S</sub> = 1 mA	0.4		1.3	V
R <sub>SS</sub> (on)	R <sub>SS</sub> (on) Static Source to Source On-State Resistance	I <sub>S</sub> = 5 A, V <sub>GS</sub> = 4.5 V	1.8	2.7	3.55	mΩ
		I <sub>S</sub> = 5 A, V <sub>GS</sub> = 3.8 V	1.9	2.8	3.65	mΩ
		I <sub>S</sub> = 5 A, V <sub>GS</sub> = 3.1 V	2.0	3.3	5.3	mΩ
	I <sub>S</sub> = 5 A, V <sub>GS</sub> = 2.5 V	2.2	4.0	7.2	mΩ	
t <sub>d</sub> (on)	Turn-ON Delay Time	V <sub>SS</sub> = 10 V, V <sub>GS</sub> = 3.8 V, I <sub>S</sub> = 5 A		13		μs
t <sub>r</sub>	Rise Time	Rg = 10 kΩ Switching Test Circuit		35		μs
t <sub>d</sub> (off)	Turn-OFF Delay Time			185		μs
t <sub>f</sub>	Fall Time			78		μs
Qg	Total Gate Charge	V <sub>SS</sub> = 10 V, V <sub>GS</sub> = 3.8 V, I <sub>S</sub> = 5 A		43		nC
$V_{F(S-S)}$	Forward Source to Source Voltage	I <sub>S</sub> = 3 A, V <sub>GS</sub> = 0 V		0.75	1.2	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

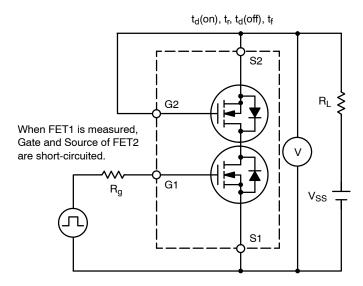


Figure 1. Switching Test Circuit

# **ORDERING INFORMATION**

Device	Marking	Package	Shipping <sup>†</sup> (Qty / Packing)
EFC4K105NUZTDG	NZ	WLCSOP10, 3.40 x 1.96 x 0.10 (Pb-Free / Halogen Free)	5,000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# **TYPICAL CHARACTERISTICS**

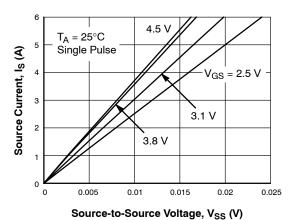


Figure 2. On-Region Characteristics

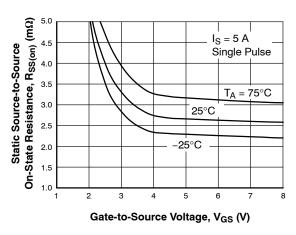


Figure 4. On-Resistance vs. Gate-to-Source Voltage

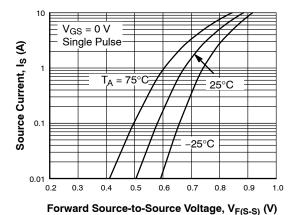


Figure 6. Forward Source-to-Source Voltage vs. Current

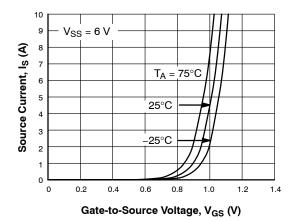


Figure 3. Transfer Characteristics

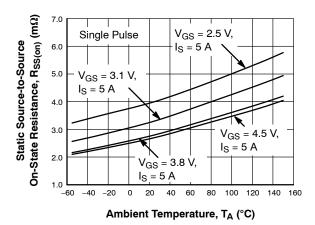


Figure 5. On-Resistance vs. Temperature

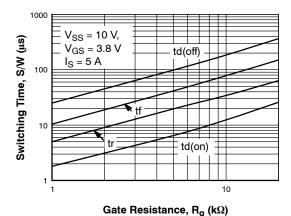


Figure 7. Switching Time vs. Gate Resistance

# **TYPICAL CHARACTERISTICS**

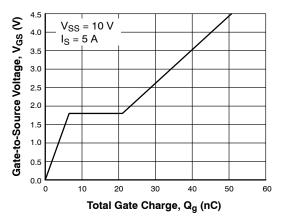


Figure 8. Gate-to-Source Voltage vs. Total Charge

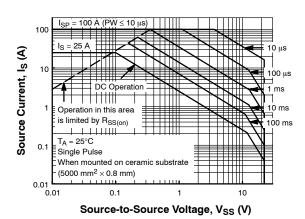


Figure 9. Safe Operating Area

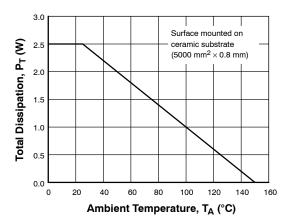


Figure 10. Total Dissipation vs. Temperature

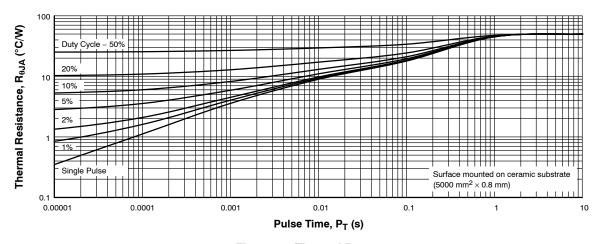


Figure 11. Thermal Response

Note on Usage: Since the EFC4K105NUZ is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.



# WLCSP10 3.40x1.96x0.10

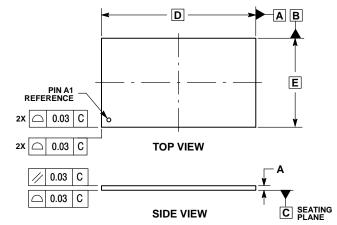
CASE 567PL ISSUE C

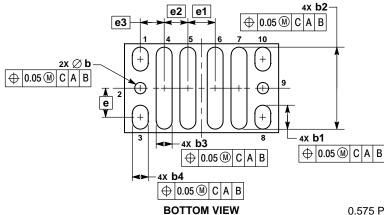
**DATE 14 MAR 2018** 

#### NOTES:

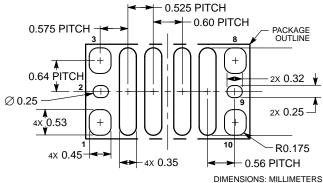
- DIMENSIONING AND TOLERANCING PER ASME Y14.5M. 1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS.

	MILLIMETERS		
DIM	MIN	NOM	MAX
Α	0.08	0.10	0.12
b	0.22	0.25	0.28
b1	0.50	0.53	0.56
b2	1.78	1.81	1.84
b3	0.32	0.35	0.38
b4	0.32	0.35	0.38
D	3.40 BSC		
E	1.96 BSC		
е	0.64 BSC		
e1	0.60 BSC		
e2	0.525 BSC		
0.3	0.525.BSC		





## RECOMMENDED SOLDERING FOOTPRINT\*



\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# GENERIC MARKING DIAGRAM\*

XX AYWZZ•

A = Assembly Location

Y = Year

W = Work Week

ZZ = Assembly Lot

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ", may or may not be present. Some products may not follow the Generic Marking.

DOCUMENT NUMBER: 98AON14524G Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.

PAGE 1 OF 1

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

onsemi, Onsemi, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at <a href="www.onsemi.com/site/pdf/Patent-Marking.pdf">www.onsemi.com/site/pdf/Patent-Marking.pdf</a>. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA class 3 medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase

#### ADDITIONAL INFORMATION

**TECHNICAL PUBLICATIONS:** 

 $\textbf{Technical Library:} \ \underline{www.onsemi.com/design/resources/technical-documentation}$ 

onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at

www.onsemi.com/support/sales

# **Mouser Electronics**

**Authorized Distributor** 

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

onsemi

EFC4K105NUZTDG